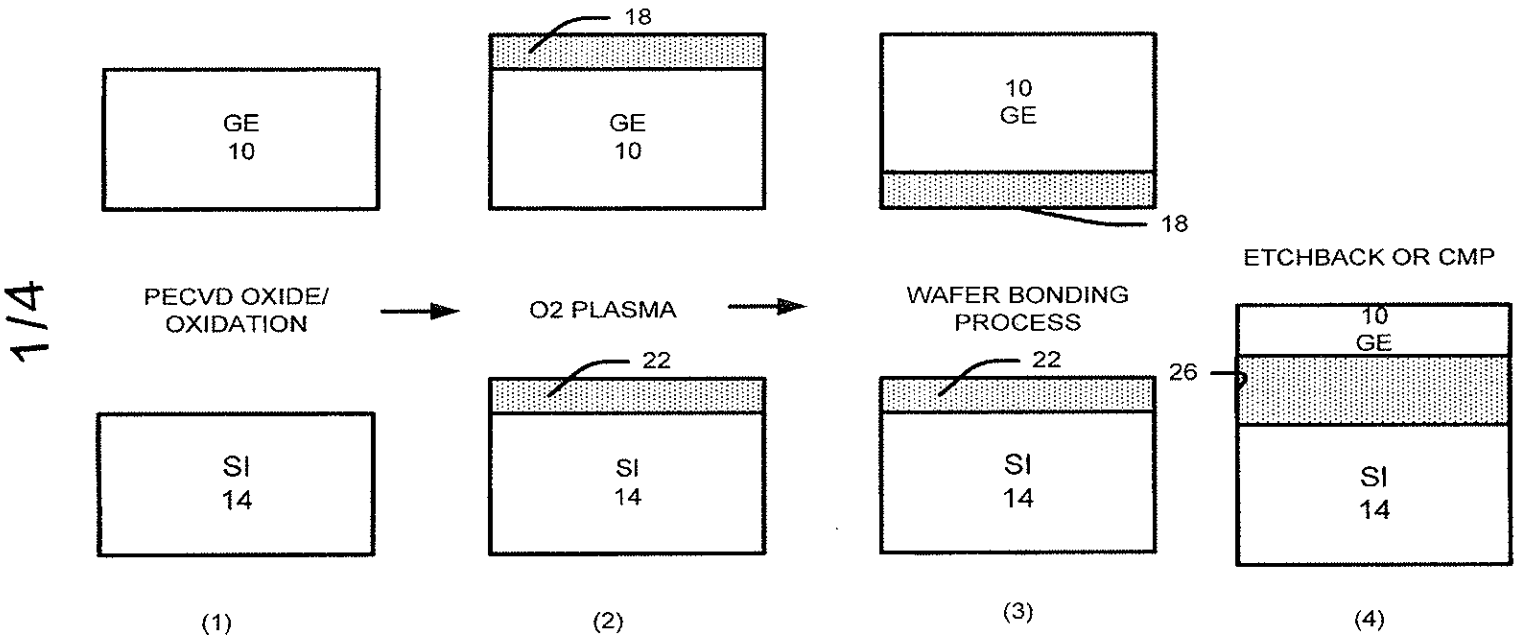

GE
10
18
GE
10
10
GE
18
ETCHBACK OR CMP
PECVD OXIDE/
OXIDATION
O2 PLASMA
WAFER BONDING
PROCESS
22
22
26
10
GE
SI
14
SI
14
SI
14
SI
14
(1)
(2)
(3)
(4)

FIGURE 1A

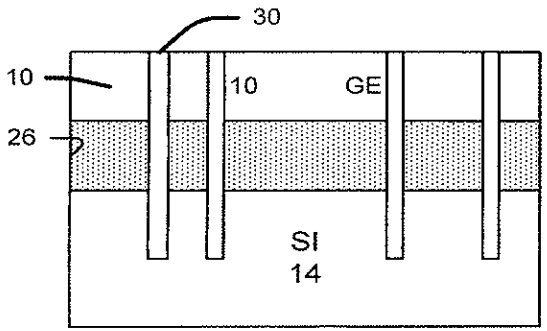


FIGURE 2

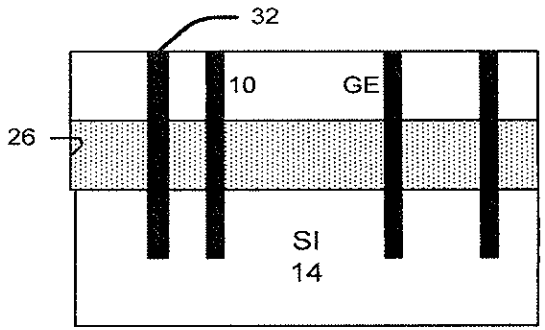


FIGURE 3

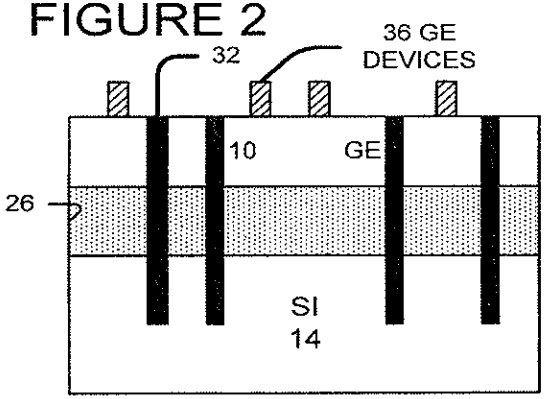


FIGURE 4

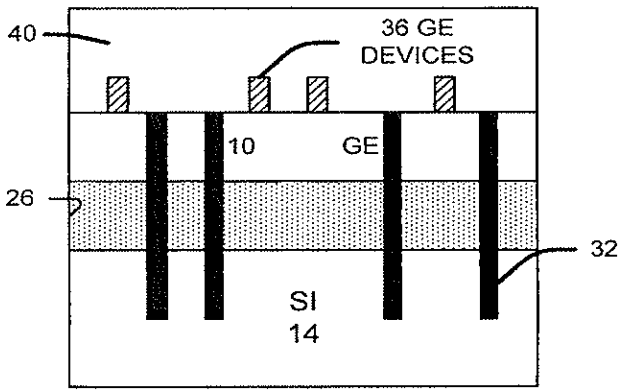


FIGURE 5

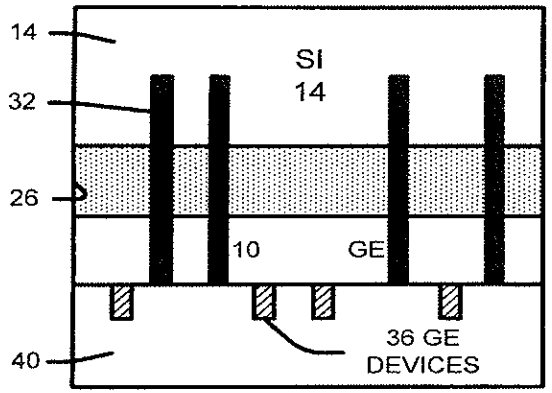


FIGURE 6

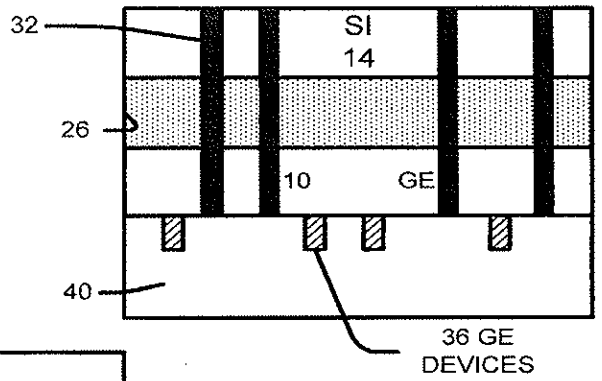


FIGURE 7

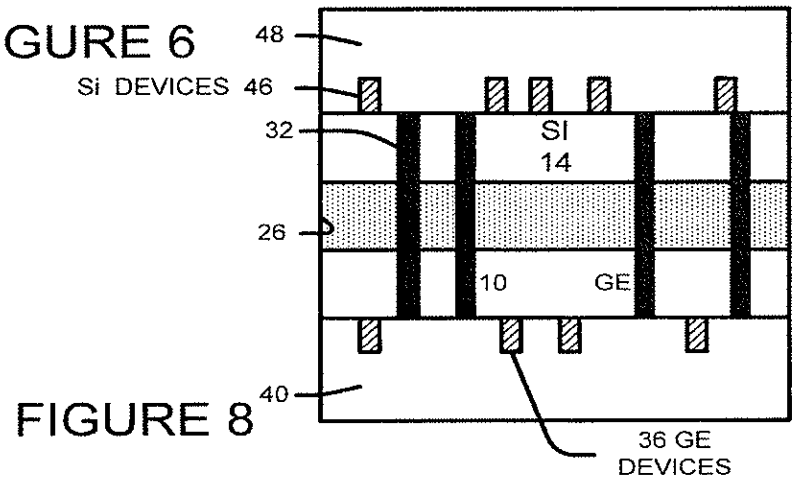


FIGURE 8

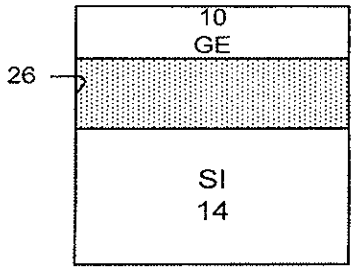


FIGURE 1B

4/4

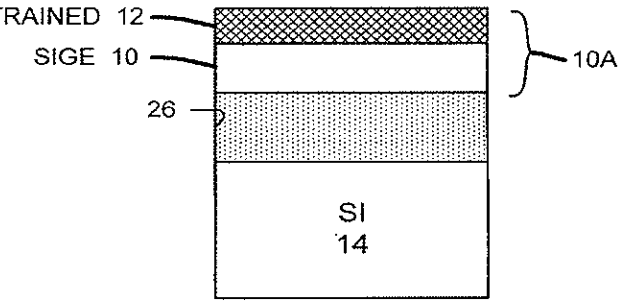


FIGURE 1C

4/4

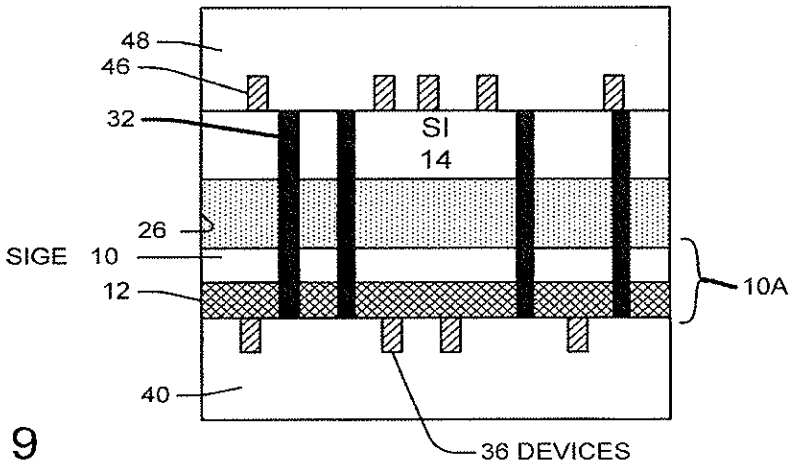


FIGURE 9